WHAT IS CLAIMED IS:

1. A blank mask comprising:

a transparent substrate, a phase shift film disposed on the transparent substrate, and a light shielding film disposed on the phase shift film,

wherein the phase shift film comprises a transition metal and silicon,

wherein the light shielding film comprises a transition metal comprising Cr and at least one of oxygen and nitrogen,

wherein a contact angle of the light shielding film measured with a pure water is 70 ° or more, and

wherein a surface energy of the light shielding film is 43.2 to 44 mN/m.

2. The blank mask of claim 1,

wherein the γ_{SL} is 22 mN/m or more.

3. The blank mask of claim 1,

wherein the light shielding film has a ratio of 0.135 to 0.16 for polar component of the surface energy compared to the surface energy of the light shielding film.

4. The blank mask of claim 1,

wherein the light shielding film comprises a first light shielding layer and a second light shielding layer disposed on the first light shielding layer.

5. The blank mask of claim 4,

wherein an amount of the transition metal of the second light shielding layer is greater than an amount of the transition metal of the first light shielding layer.

6. The blank mask of claim 1,

wherein the light shielding film further comprises at least one selected from the group consisting of Ta, Ti, and Hf.